



SSCU1RN30GS8

N-Channel Small Switching MOSFET with ESD Protection

➤ Features

V_{DS}	V_{GS}	$R_{DS(ON)}$ Typ.	I_D	ESD
30V	$\pm 12V$	$1\Omega@10V$	0.6A	500V
		$1.2\Omega@4V5$		
		$1.7\Omega@2V5$		

➤ Description

This device is an N-Channel enhancement mode MOSFET, with low on-resistance, fast switching speed and low threshold voltage, it is ideal for portable equipment.

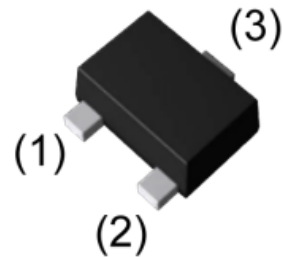
➤ Applications

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers
- Display, Memories, Transistors, etc.
- Battery Operated System
- Solid-State Relays

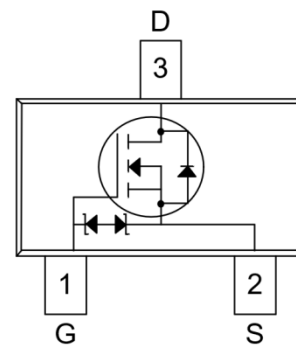
➤ Ordering Information

Device	Package	Shipping
SSCU1RN30GS8	SOT-523	3000/Reel

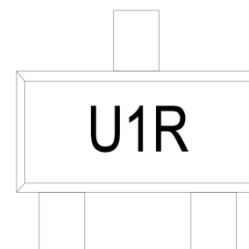
➤ Pin configuration



SOT-523



Pin Configuration (Top View)



Marking



➤ **Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)**

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain-to-Source Voltage	30	V
V_{GSS}	Gate-to-Source Voltage	± 12	V
I_{D}	Continuous Drain Current ^a	0.6	A
I_{DM}	Pulsed Drain Current ^b	2.4	A
P_{D}	Power Dissipation ^c	0.6	W
T_{J}	Operation junction temperature	$-55\sim 150$	$^{\circ}\text{C}$
T_{STG}	Storage temperature range	$-55\sim 150$	$^{\circ}\text{C}$

➤ **Thermal Resistance Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)**

Symbol	Parameter	Maximum	Unit
$R_{\theta\text{JA}}$	Junction-to-Ambient Thermal Resistance ^a	260	$^{\circ}\text{C}/\text{W}$

Note:

- The value of $R_{\theta\text{JA}}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user is specific board design. The power dissipation is based on the $t\leq 10\text{s}$ thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation P_{D} is based on $T_{\text{J(MAX)}}=150^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

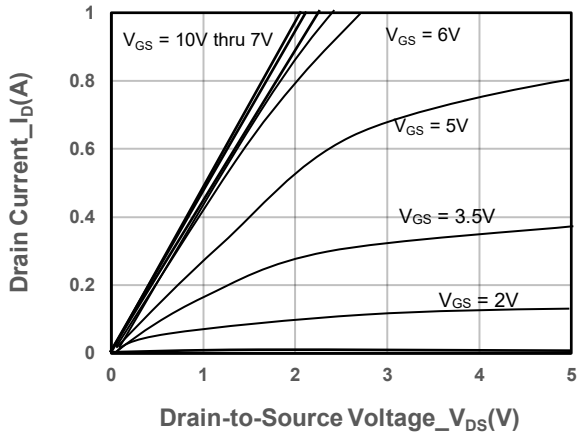


➤ **Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)**

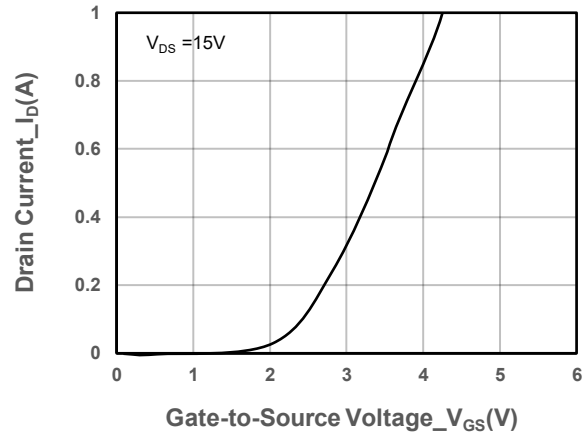
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.75	1	1.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.5A$		1	1.5	Ω
		$V_{GS} = 4.5V, I_D = 0.5A$		1.2	1.8	
		$V_{GS} = 2.5V, I_D = 0.2A$		1.7	3.5	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$			1	μA
Gate-Source Leak Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 10	μA
Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 0.2A$			1.3	V
Input Capacitance	C_{ISS}	$V_{DS} = 15V, V_{GS} = 0V,$ $f = 1MHz$		33		pF
Output Capacitance	C_{OSS}			6.8		
Reverse Transfer Capacitance	C_{RSS}			4.8		
Turn-on Delay Time	$T_{D(ON)}$	$V_{GS} = 10V, V_{DS} = 10V,$ $I_D = 0.1A$		25		ns
Rise Time	T_r			10		
Turn-off Delay Time	$T_{D(OFF)}$			35		
Fall Time	T_f			20		
Total Gate Charge	Q_G	$V_{GS} = 10V, V_{DS} = 15V,$ $I_D = 0.2A$		1		nC
Gate to Source Charge	Q_{GS}			0.12		
Gate to Drain Charge	Q_{GD}			0.12		



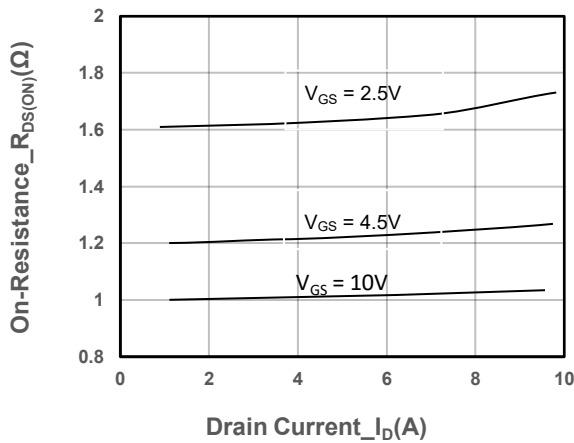
➤ Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)



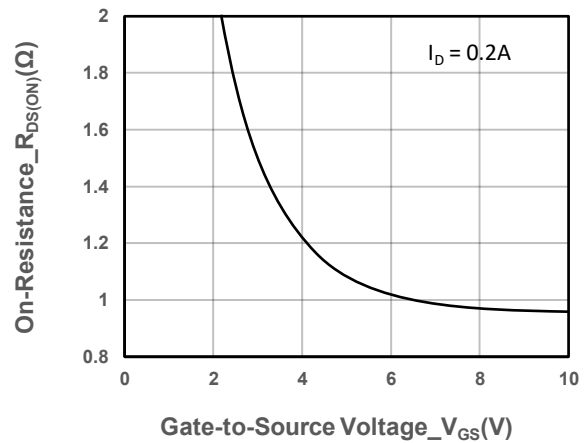
Output Characteristics



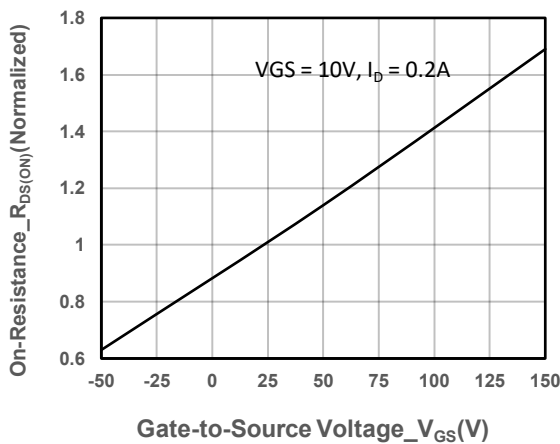
Transfer Characteristics



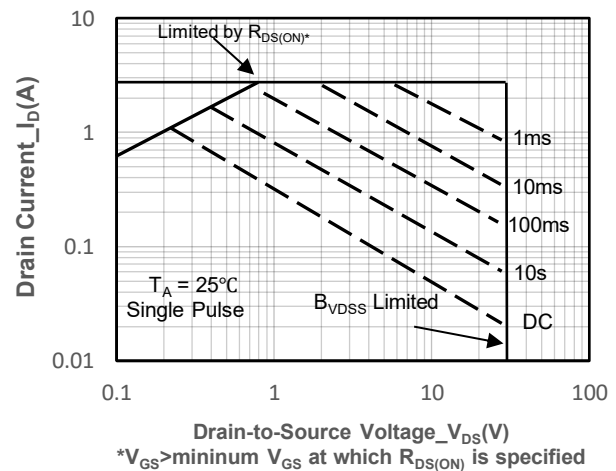
On-Resistance vs. Drain Current and Gate Voltage



On-Resistance vs. Gate-to-Source Voltage

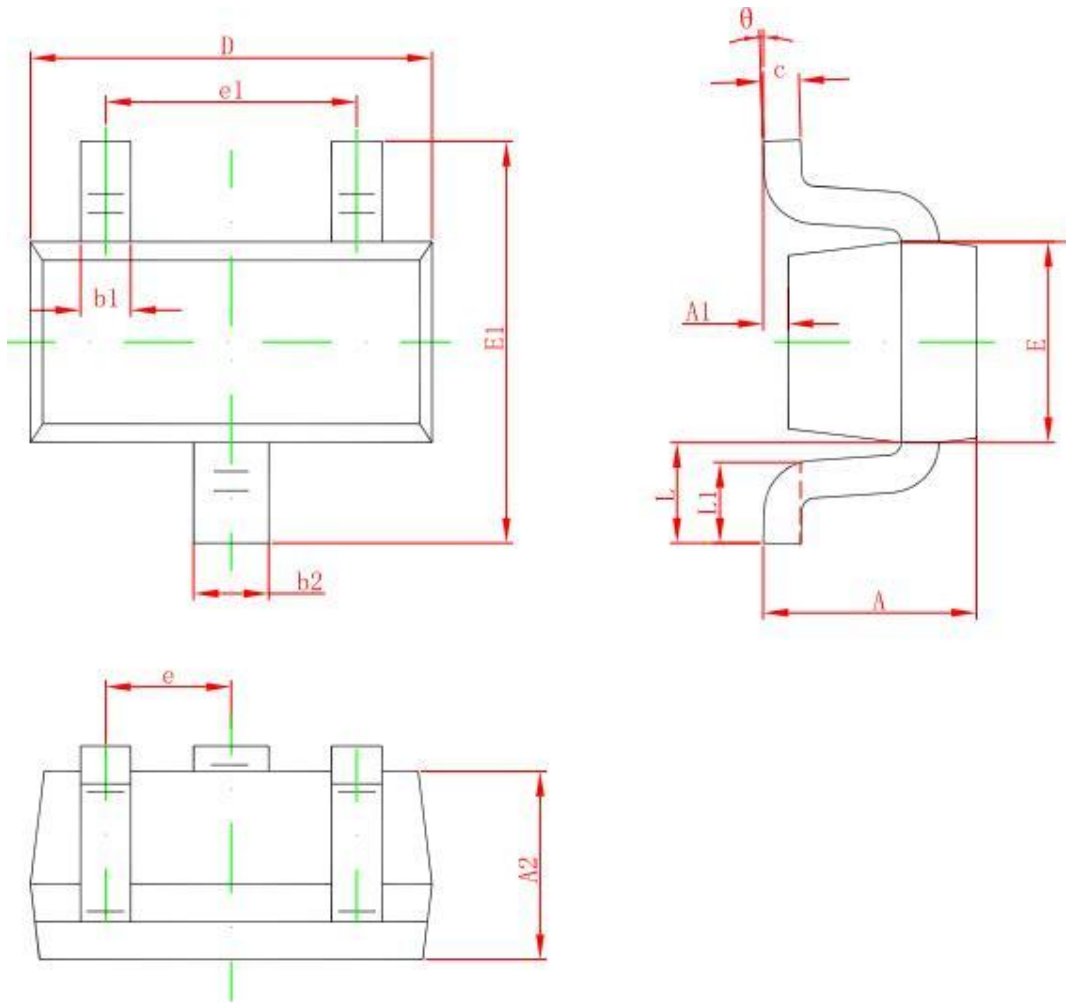


On-Resistance vs. Junction Temperature



Safe Operating Area vs. Junction-to-Ambient

➤ Package Information



Symbol	MILL IMETER		Symbol	MILL IMETER	
	Min	Max		Min	Max
A	0.70	0.90	E	0.70	0.90
A1	0.00	0.10	E1	1.45	1.75
A2	0.70	0.80	e	0.50Typ	
b1	0.15	0.25	e1	0.90	1.10
b2	0.25	0.35	L	0.40Ref	
c	0.08	0.20	L1	0.20	0.46
D	1.50	1.70	θ	0°	8°



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